

# E0C6S27

## **4-bit Single Chip Microcomputer**



- Core CPU Architecture
- SVD Circuit
- High Quality Display LCD Driver
- Stepping-Motor Driver

## ■ DESCRIPTION

The E0C6S27 is an advanced single-chip CMOS 4-bit microcomputer consisting of the E0C6200A CMOS 4-bit core CPU. It also contains the ROM, RAM, LCD driver, time base counter, stopwatch counter, and stepping-motor driver. The E0C6S27 provides an excellent solution for application as digital-analog-combinational watch.

## ■ FEATURES

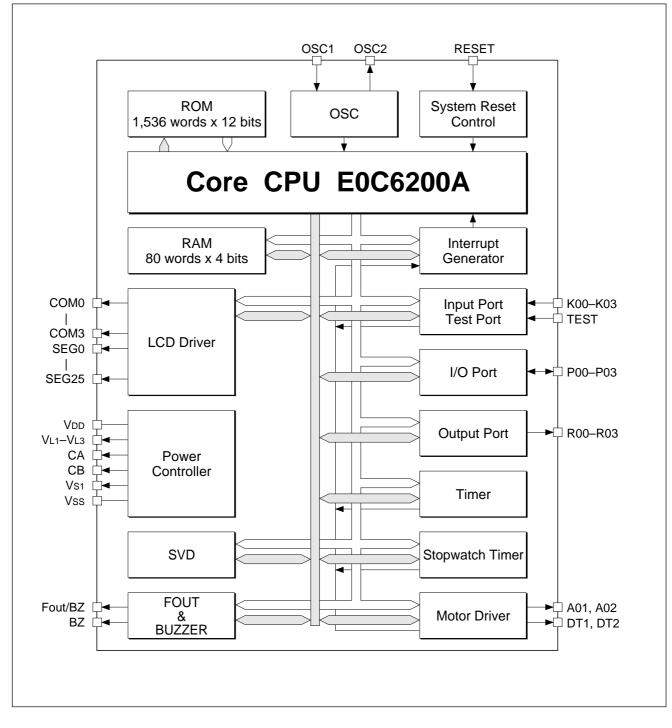
<ul> <li>CMOS LSI 4-bit parallel processing</li> </ul>	
Clock	32.768kHz for Crystal or CR oscillation circuit
● Instruction set	100 instructions
Instruction execution time	153µsec, 214µsec, 366µsec at 32.768kHz mode
● ROM size	1,536 $\times$ 12 bits
● RAM size	$80 \times 4$ bits
Input port	4 bits (pull down resistors are available by mask option)
Output port	4 bits (general purpose)
● I/O port	4 bits
● LCD driver	26 segments $\times$ 2/3/4 commons
• Timer	Clock timer / Stopwatch timer
<ul> <li>Built-in stopwatch timer</li> </ul>	
<ul> <li>Supply voltage detection (SVD) circuit</li> </ul>	1.2V / 2.4V
<ul> <li>Interrupts</li> </ul>	External : Input interrupt 1 system Internal : Timer interrupt 2 systems Motor driver interrupt 1 system
• Current consumption	HALT mode (32.768kHz/3.0V): 1.0µA (Typ.)
Package	QFP6-60pin (plastic) Die form

## ■ LINE UP

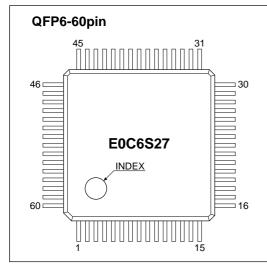
Model	Supply voltage	Oscillator
E0C6S27 (Normal type)	2.2 to 3.6V	32.768kHz Crystal or 65kHz CR (Typ.)
E0C6SA27 (High speed type)	2.2 to 3.6V	200kHz CR (Typ.)
E0C6SB27 (Wide voltage type)	0.9 to 3.6V	32.768kHz Crystal or 65kHz CR (Typ.)
E0C6SL27 (Low voltage type)	0.9 to 1.8V	32.768kHz Crystal

## **SEIKO EPSON CORPORATION**

## BLOCK DIAGRAM



## ■ PIN CONFIGURATION



Pin No.	Pin name						
1	OSC1	16	COM2	31	TEST	46	P01
2	OSC2	17	COM3	32	SEG13	47	P02
3	N.C.	18	SEG0	33	SEG14	48	P03
4	Vs1	19	SEG1	34	SEG15	49	RESET
5	CA	20	SEG2	35	SEG16	50	K00
6	СВ	21	SEG3	36	SEG17	51	K01
7	VL1	22	SEG4	37	SEG18	52	K02
8	Vl2	23	SEG5	38	SEG19	53	K03
9	Vl3	24	SEG6	39	SEG20	54	R00
10	DT1	25	SEG7	40	SEG21	55	R01
11	A01	26	SEG8	41	SEG22	56	R02
12	A02	27	SEG9	42	SEG23	57	R03
13	DT2	28	SEG10	43	SEG24	58	N.C.
14	COM0	29	SEG11	44	SEG25	59	Vss
15	COM1	30	SEG12	45	P00	60	Vdd

N.C. : No Connection

## ■ PIN DESCRIPTION

Pin name	Pin No.	I/O	Function
Vdd	60	(I)	Power supply pin (+)
Vss	59	(I)	Power supply pin (–)
Vs1	4	0	Oscillation and internal logic system regulated voltage output pin
VL1	7	0	LCD system regulated voltage output pin (-1.05V)
VL2	8	0	LCD system booster voltage output pin (VL1×2)
VL3	9	0	LCD system booster voltage output pin (VL1×3)
CA, CB	5, 6	_	Voltage booster capacitor connecting pin
OSC1	1	I	Crystal or CR oscillation input pin
OSC2	2	0	Crystal or CR oscillation output pin
K00–K03	50–53	I	Input port pin
P00-P03	45–48	I/O	I/O port pin
R00–R03	54–57	0	Output port pin
SEG0-SEG25	18–30, 32–44	0	LCD segment output pin
COM0–COM3	14–17	0	LCD common output pin
RESET	49	Ι	Initial reset input pin
TEST	31	Ι	Testing input pin
DT1, DT2	10, 13	I/O	Test pin
A01, A02	11, 12	0	Motor driving port pin

## ■ ELECTRICAL CHARACTERISTICS

## • Absolute Maximum Ratings

Absolute Maximum Ratii	ngs		(Vdd=0V)
Rating	Symbol	Value	Unit
Supply voltage	Vss	-5.0 to 0.5	V
Input voltage (1)	VI	Vss - 0.3 to 0.5	V
Input voltage (2)	Viosc	Vss - 0.3 to 0.5	V
Operating temperature	Topr	-20 to 70	O°
Storage temperature	Tstg	-65 to 150	O°
Soldering temperature / Time	Tsol	260°C, 10sec (lead section)	-
Permissible dissipation *1	PD	250	mW

\*1: In case of plastic package (QFP6-60pin).

## • Recommended Operating Conditions

#### E0C6S27

E0C6S27					(Ta=-20	to 70°C)
Condition	Symbol	Remark	Min.	Тур.	Max.	Unit
Supply voltage	Vss	VDD=0V	-3.6	-3.0	-2.2	V
Oscillation frequency	fosc	Crystal oscillation		32.768		kHz
		CR oscillation, R=470kΩ		65	80	kHz
Booster capacitor	C1		0.1			μF
Capacitor between VDD and VL1	C2		0.1			μF
Capacitor between VDD and VL2	C3		0.1			μF
Capacitor between VDD and VL3	C4		0.1			μF
Capacitor between VDD and VS1	C5		0.1			μF

## FOC6SA27

E0C6SA27					(Ta=-20	to 70°C)
Condition	Symbol	Remark	Min.	Тур.	Max.	Unit
Supply voltage	Vss	VDD=0V	-3.6	-3.0	-2.2	V
Oscillation frequency	fosc	CR oscillation, R=160kΩ		200	260	kHz
Booster capacitor	C1		0.1			μF
Capacitor between VDD and VL1	C2		0.1			μF
Capacitor between VDD and VL2	C3		0.1			μF
Capacitor between VDD and VL3	C4		0.1			μF
Capacitor between VDD and VS1	C5		0.1			μF

#### E0C6SI 27

E0C6SL27					(Ta=-20	to 70°C)
Condition	Symbol	Remark	Min.	Тур.	Max.	Unit
Supply voltage	Vss	VDD=0V *3	-1.8	-1.5	-1.1	V
		VDD=0V, With software control *1	-1.8	-1.5	-0.9 *2	V
Oscillation frequency	fosc			32.768		kHz
Booster capacitor	C1		0.1			μF
Capacitor between VDD and VL1	C2		0.1			μF
Capacitor between VDD and VL2	C3		0.1			μF
Capacitor between VDD and VL3	C4		0.1			μF
Capacitor between VDD and VS1	C5		0.1			μF

\*1: When the heavy load protection mode is set by software and the SVD circuit is turned off.

\*2: The voltage which can be displayed on the LCD panel will differ according to the characteristics of the LCD panel.

\*3: When there is no software control during CR oscillation or crystal oscillation.

## ENC6SB27

EUC03D2/					(Ta=-20	to 70°C)
Condition	Symbol	Remark	Min.	Тур.	Max.	Unit
Supply voltage	Vss	VDD=0V *3	-3.6	-3.0	-1.1	V
		VDD=0V, With software control *1	-3.6	-3.0	-0.9 *2	V
Oscillation frequency	fosc	Crystal oscillation		32.768		kHz
		CR oscillation, R=470k $\Omega$		65	80	kHz
Booster capacitor	C1		0.1			μF
Capacitor between VDD and VL1	C2		0.1			μF
Capacitor between VDD and VL2	C3		0.1			μF
Capacitor between VDD and VL3	C4		0.1			μF
Capacitor between VDD and VS1	C5		0.1			μF

\*1: When the heavy load protection mode is set by software and the SVD circuit is turned off.

\*2: The voltage which can be displayed on the LCD panel will differ according to the characteristics of the LCD panel.

\*3: When there is no software control during CR oscillation or crystal oscillation.



## • DC Characteristics E0C6S27/6SA27/6SB27

(Unless otherwise specified: VDD=0V, Vss=-3.0V, fosc=32.768kHz, Ta=25°C, Vs1/VL1–VL3 are internal voltage, C1–C5=0.1μF)								
Characteristic	Symbol	Condition		Min.	Тур.	Max.	Unit	
High level input voltage (1)	VIH1		K00–K03, P00–P03	0.2•Vss		0	V	
High level input voltage (2)	VIH2		RESET, TEST	0.15•Vss		0	V	
Low level input voltage (1)	VIL1		K00–K03, P00–P03	Vss		0.8•Vss	V	
Low level input voltage (2)	VIL2		RESET, TEST	Vss		0.85•Vss	V	
High level input current (1)	IIH1	VIH1=0V, No pull down resistor	K00–K03, P00–P03	0		0.5	μΑ	
High level input current (2)	IIH2	VIH2=0V, With pull down resistor	K00–K03	10		40	μA	
High level input current (3)	Іінз	VIH3=0V, With pull down resistor	P00-P03	30		100	μA	
			RESET, TEST					
Low level input current	lı∟	VIL=VSS	K00–K03, P00–P03	-0.5		0	μΑ	
			RESET, TEST					
High level output current (1)	Іон1	Voн1=0.1•Vss	R02, R03, P00–P03			-1.0	mA	
High level output current (2)	Іон2	VoH2=0.1•Vss	R00, R01			-1.0	mA	
		(built-in protection resistance)						
Low level output current (1)	IOL1	Vol1=0.9•Vss	R02, R03, P00–P03	3.0			mA	
Low level output current (2)	IOL2	Vol2=0.9•Vss	R00, R01	3.0			mA	
		(built-in protection resistance)						
Common output current	Іонз	Vонз=-0.05V	COM0–COM3			-3	μΑ	
	IOL3	Vol3=Vl3+0.05V		3			μΑ	
Segment output current	Іон4	Vон4=-0.05V	SEG0-SEG25			-3	μΑ	
(during LCD output)	IOL4	Vol4=Vl3+0.05V		3			μΑ	
Segment output current	Іон5	Voн5=0.1•Vss	SEG0-SEG25			-300	μΑ	
(during DC output)	IOL5	Vol5=0.9•Vss		300			μA	

#### (Unless otherwise specified: Von=0V, Vss=-3.0V, fosc=32.768kHz, Ta=25°C, Vs1/Vi 1–Vi 3 are internal voltage, C1–C5–0.1uE)

#### E0C6SL27

(Unless otherwi	se specifi	ed: VDD=0V, Vss=-1.5V, fosc=32.	768kHz, Ta=25°C, Vs1	/VL1-VL3 are	internal vo	ltage, C1–C5	5=0.1μF)
Characteristic	Symbol	Condition		Min.	Тур.	Max.	Unit
High level input voltage (1)	VIH1		K00–K03, P00–P03	0.2•Vss		0	V
High level input voltage (2)	VIH2		RESET, TEST	0.15•Vss		0	V
Low level input voltage (1)	VIL1		K00–K03, P00–P03	Vss		0.8•Vss	V
Low level input voltage (2)	VIL2		RESET, TEST	Vss		0.85•Vss	V
High level input current (1)	IIH1	VIH1=0V, No pull down resistor	K00–K03, P00–P03	0		0.5	μΑ
High level input current (2)	IIH2	VIH2=0V, With pull down resistor	K00–K03	5		20	μA
High level input current (3)	Іінз	VIH3=0V, With pull down resistor	P00–P03	10		60	μΑ
			RESET, TEST				
Low level input current	lı∟	VIL=VSS	K00–K03, P00–P03	-0.5		0	μΑ
-			RESET, TEST				
High level output current (1)	Іон1	VOH1=0.1•Vss	R02, R03, P00–P03			-200	μA
High level output current (2)	Іон2	VoH2=0.1•Vss	R00, R01			-200	μA
		(built-in protection resistance)					
Low level output current (1)	IOL1	Vol1=0.9•Vss	R02, R03, P00–P03	700			μΑ
Low level output current (2)	IOL2	Vol2=0.9•Vss	R00, R01	700			μA
		(built-in protection resistance)					
Common output current	Іонз	Vонз=-0.05V	COM0–COM3			-3	μΑ
	IOL3	Vol3=Vl3+0.05V		3			μA
Segment output current	Іон4	Vон4=-0.05V	SEG0-SEG25			-3	μA
(during LCD output)	IOL4	Vol4=Vl3+0.05V		3			μA
Segment output current	Іон5	Voh5=0.1•Vss	SEG0-SEG25			-100	μA
(during DC output)	IOL5	Vol5=0.9•Vss		130			μA

## • Analog Circuit Characteristics and Current Consumption

#### E0C6S27 (Crystal, Normal Operating Mode)

(Unless otherwise specified: VDD=0V, Vss=-3.0V, fosc=32.768kHz, Ta=25°C, Cg=25pF, Vs1/VL1-VL3 are internal voltage, C1-C5=0.1µF)

Characteristic	Symbol	Condition		Min.	Тур.	Max.	Unit
Internal voltage	VL1	Connect $1M\Omega$ load resistor betw (without panel load)	1 2•VL2-0.1		$\frac{1}{2}$ •VL2×0.9	V	
	VL2	Connect $1M\Omega$ load resistor betw (without panel load)	-2.25	-2.10	-1.95	V	
	Vl3	Connect $1M\Omega$ load resistor betw (without panel load)	3 2•VL2-0.1		3 2•VL2×0.9	V	
SVD voltage	Vsvd			-2.55	-2.40	-2.25	V
SVD circuit response time	tsvd					100	μS
Current consumption	IOP	During HALT			0.7	1.4	μΑ
		During execution *1	Without panel load		1.9	3.5	μΑ

\*1: The SVD circuit is turned off.

## E0C6S27 (Crystal, Heavy Load Protection Mode)

(Unless otherwise specified: VDD=0V, Vss=-3.0V, fosc=32.768kHz, Ta=25°C, Cg=25pF, Vs1/VL1-VL3 are internal voltage, C1-C5=0.1µF)

Characteristic	Symbol	Condition		Min.	Тур.	Max.	Unit
Internal voltage	VL1	Connect $1M\Omega$ load resistor betw	een VDD and VL1	1-0-VL2-0.1		1 •VL2×0.85	V
		(without panel load)		2 2 0.1		2 12×0.05	v
	VL2	Connect $1M\Omega$ load resistor betw	een VDD and VL2	-2.25	-2.10	-1.95	V
		(without panel load)		-2.20	-2.10	-1.55	v
	VL3	Connect $1M\Omega$ load resistor betw	een VDD and VL3	3 •VL2-0.1		3 •VL2×0.85	V
		(without panel load)		2 2 0.1		2 12×0.05	v
SVD voltage	Vsvd			-2.55	-2.40	-2.25	V
SVD circuit response time	tsvd					100	μS
Current consumption	IOP	During HALT			5.0	15	μΑ
		During execution *1	Without panel load		6.5	19	μΑ

\*1: The SVD circuit is turned off.

### E0C6SL27 (Crystal, Normal Operating Mode)

(Unless otherwise specified: VDD=0V, Vss=-1.5V, fosc=32.768kHz, Ta=25°C, CG=25pF, Vs1/VL1–VL3 are internal voltage, C1–C5=0.1µF)

Characteristic	Symbol	Condition		Min.	Тур.	Max.	Unit
Internal voltage	VL1	Connect $1M\Omega$ load resistor betw	een VDD and VL1	-1.15	-1.05	-0.95	V
		(without panel load)		-1.15	-1.05	-0.35	v
	VL2	Connect $1M\Omega$ load resistor betw	een VDD and VL2	2•VL1-0.1		2•VL1×0.9	V
		(without panel load)		2.001		2.011.0.9	v
	VL3	Connect $1M\Omega$ load resistor betw	een VDD and VL3	3•VL1-0.1		3•VL1×0.9	V
		(without panel load)		3•VLI-0.1		3•VLIX0.9	v
SVD voltage	Vsvd			-1.30	-1.20	-1.10	V
SVD circuit response time	tsvd					100	μS
Current consumption	IOP	During HALT			0.6	1.1	μA
		During execution *1	Without panel load		1.7	3.0	μΑ

\*1: The SVD circuit is turned off.

## E0C6SL27 (Crystal, Heavy Load Protection Mode)

(Unless otherwise specified: VDD=0V, Vss=-1.5V, fosc=32.768kHz, Ta=25°C, CG=25pF, Vs1/VL1-VL3 are internal voltage, C1-C5=0.1µF)

Characteristic	Symbol	Condition	·	Min.	Тур.	Max.	Unit
Internal voltage	VL1	Connect $1M\Omega$ load resistor betwork (without panel load)	een VDD and VL1	-1.15	-1.05	-0.95	V
	VL2	Connect $1M\Omega$ load resistor betw (without panel load)	een VDD and VL2	2•VL1-0.1		2•VL1×0.85	V
	VL3	Connect $1M\Omega$ load resistor betw (without panel load)	hect 1M $\Omega$ load resistor between VDD and VL3			3•VL1×0.85	V
SVD voltage	Vsvd			-1.30	-1.20	-1.10	V
SVD circuit response time	tsvd					100	μS
Current consumption	IOP	During HALT			1.2	2.2	μA
		During execution *1	Without panel load		3.4	6.0	μΑ

\*1: The SVD circuit is turned off.

## **EPSON**

## E0C6SB27 (Crystal, Normal Operating Mode)

(Unless otherwise specified: VDD=0V, Vss=-3.0V, fosc=32.768kHz, Ta=25°C, Cg=25pF, Vs1/VL1-VL3 are internal voltage, C1-C5=0.1µF)

Characteristic	Symbol	Condition		Min.	Тур.	Max.	Unit
Internal voltage	VL1	Connect $1M\Omega$ load resistor betw (without panel load)	,		-1.05	-0.95	V
	VL2	Connect $1M\Omega$ load resistor betw (without panel load)	een VDD and VL2	2•VL1-0.1		2•VL1×0.9	V
	VL3	Connect $1M\Omega$ load resistor betw (without panel load)	ect 1M $\Omega$ load resistor between VDD and VL3 3•V/			3•VL1×0.9	V
SVD voltage	Vsvd			-1.30	-1.20	-1.10	V
SVD circuit response time	tsvd					100	μS
Current consumption	IOP	During HALT			0.7	1.4	μΑ
		During execution *1	Without panel load		1.9	3.5	μΑ

\*1: The SVD circuit is turned off.

## E0C6SB27 (Crystal, Heavy Load Protection Mode)

(Unless otherwise specified: VDD=0V, Vss=-3.0V, fosc=32.768kHz, Ta=25°C, Cg=25pF, Vs1/VL1-VL3 are internal voltage, C1-C5=0.1µF)

Characteristic	Symbol	Condition	1	Min.	Тур.	Max.	Unit
Internal voltage	VL1	Connect $1M\Omega$ load resistor betw (without panel load)	een VDD and VL1	-1.15	-1.05	-0.95	V
	VL2	Connect $1M\Omega$ load resistor betw (without panel load)	een VDD and VL2	2•VL1-0.1		2•VL1×0.85	V
	VL3	Connect $1M\Omega$ load resistor betw (without panel load)	een VDD and VL3	3•VL1-0.1		3•VL1×0.85	V
SVD voltage	Vsvd			-1.30	-1.20	-1.10	V
SVD circuit response time	tsvd					100	μS
Current consumption	IOP	During HALT			1.4	2.8	μΑ
		During execution *1	Without panel load		3.8	7.0	μΑ

\*1: The SVD circuit is turned off.

## E0C6S27 (CR, Normal Operating Mode)

(Unless otherwise specified: VDD=0V, Vss=-3.0V, fosc=65kHz, Rcr=470kΩ, Ta=25°C, Vs1/VL1-VL3 are internal voltage, C1-C5=0.1µF)

Characteristic	Symbol	Condition		Min.	Тур.	Max.	Unit
Internal voltage	VL1	Connect $1M\Omega$ load resistor betw	een VDD and VL1	1-VL2-0.1		$\frac{1}{2} V_{L2 \times 0.9}$	V
		(without panel load)		2		2 2	v
	VL2	Connect $1M\Omega$ load resistor betw	een VDD and VL2	-2.25	-2.10	-1.95	V
		(without panel load)		-2.25	-2.10	-1.95	v
	VL3	Connect $1M\Omega$ load resistor betw	een VDD and VL3	3 •VL2-0.1		3 •VL2×0.9	V
		(without panel load)		2 2 0.1		2 12×0.9	v
SVD voltage	Vsvd			-2.55	-2.40	-2.25	V
SVD circuit response time	tsvd					100	μS
Current consumption	IOP	During HALT			6.5	14.0	μΑ
		During execution *1	Without panel load		9.0	18.0	μΑ

\*1: The SVD circuit is turned off.

## E0C6S27 (CR, Heavy Load Protection Mode)

(Unless otherwise specified: VDD=0V, Vss=-3.0V, fosc=65kHz, Rcr=470kΩ, Ta=25°C, Vs1/VL1-VL3 are internal voltage, C1-C5=0.1µF)

Characteristic	Symbol	Condition		Min.	Тур.	Max.	Unit
Internal voltage	VL1	Connect 1MΩ load resistor betw	een VDD and VL1	1-VL2-0.1		1 •VL2×0.85	V
		(without panel load)		2 2		2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	v
	VL2	Connect $1M\Omega$ load resistor betw	een VDD and VL2	-2.25	-2.10	-1.95	V
		(without panel load)		-2.25	-2.10	-1.95	v
	VL3	Connect $1M\Omega$ load resistor betw	een VDD and VL3	3-VL2-0.1		3 •VL2×0.85	V
		(without panel load)		2		2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	v
SVD voltage	Vsvd			-2.55	-2.40	-2.25	V
SVD circuit response time	tsvd					100	μS
Current consumption	IOP	During HALT			16.0	35.0	μΑ
		During execution *1	Without panel load		18.0	40.0	μΑ

\*1: The SVD circuit is turned off.

## E0C6SA27 (CR, Normal Operating Mode)

(Unless otherwise specified: VDD=0V, Vss=-3.0V, fosc=200kHz, Rcr=160kΩ, Ta=25°C, Vs1/VL1-VL3 are internal voltage, C1-C5=0.1µF)

Characteristic	Symbol	Condition		Min.	Тур.	Max.	Unit
Internal voltage	VL1	Connect $1M\Omega$ load resistor betw	een VDD and VL1	1-VL2-0.1		$\frac{1}{2} V_{L2 \times 0.9}$	V
		(without panel load)		2 2 0.1		2 12×0.9	v
	VL2	Connect $1M\Omega$ load resistor betw	een VDD and VL2	-2.25	-2.10	-1.95	V
		(without panel load)		-2.25	-2.10	-1.95	v
	VL3	Connect $1M\Omega$ load resistor betw	een VDD and VL3	3 •VL2-0.1		$\frac{3}{2} V_{L2 \times 0.9}$	V
		(without panel load)		2		2 2 2	v
SVD voltage	Vsvd			-2.55	-2.40	-2.25	V
SVD circuit response time	tsvd					100	μS
Current consumption	IOP	During HALT			60	110	μA
		During execution *1	Without panel load		70	130	μA

\*1: The SVD circuit is turned off.

#### E0C6SA27 (CR, Heavy Load Protection Mode)

(Unless otherwise specified: VDD=0V, Vss=-3.0V, fosc=200kHz, Rcr=160kΩ, Ta=25°C, Vs1/VL1-VL3 are internal voltage, C1-C5=0.1µF)

Characteristic	Symbol	Condition		Min.	Тур.	Max.	Unit
Internal voltage	VL1	Connect $1M\Omega$ load resistor betwee (without panel load)	een VDD and VL1	1 2•VL2-0.1		1 2•VL2×0.85	V
	VL2	Connect $1M\Omega$ load resistor betwee (without panel load)	een VDD and VL2	-2.25	-2.10	-1.95	V
	VL3	Connect $1M\Omega$ load resistor betwee (without panel load)	een VDD and VL3	3 2•VL2-0.1		3 2•VL2×0.85	V
SVD voltage	Vsvd			-2.55	-2.40	-2.25	V
SVD circuit response time	tsvd					100	μS
Current consumption	IOP	During HALT	MCth and a secold secol		85	160	μΑ
		During execution *1	Without panel load		95	180	μΑ

\*1: The SVD circuit is turned off.

## E0C6SB27 (CR, Normal Operating Mode)

(Unless otherwise specified: VDD=0V, Vss=-3.0V, fosc=65kHz, RcR=470kΩ, Ta=25°C, Vs1/VL1-VL3 are internal voltage, C1-C5=0.1μF)

Characteristic	Symbol	Condition		Min.	Тур.	Max.	Unit
Internal voltage	VL1	Connect $1M\Omega$ load resistor betw (without panel load)	een VDD and VL1	-1.15	-1.05	-0.95	V
	VL2	Connect $1M\Omega$ load resistor betw (without panel load)	een VDD and VL2	2•VL1-0.1		2•VL1×0.9	V
	VL3	Connect $1M\Omega$ load resistor betw (without panel load)	een VDD and VL3	3•VL1-0.1		3•VL1×0.9	V
SVD voltage	Vsvd			-1.30	-1.20	-1.10	V
SVD circuit response time	tsvd					100	μS
Current consumption	IOP	During HALT	M <sup>2</sup> th such a second loss of		6.5	14.0	μΑ
		During execution *1	Without panel load		9.0	18.0	μΑ

\*1: The SVD circuit is turned off.

### E0C6SB27 (CR, Heavy Load Protection Mode)

(Unless otherwise specified: VDD=0V, Vss=-3.0V, fosc=65kHz, RcR=470kΩ, Ta=25°C, Vs1/VL1–VL3 are internal voltage, C1–C5=0.1µF)

Characteristic	Symbol	Condition		Min.	Тур.	Max.	Unit
Internal voltage	VL1	Connect $1M\Omega$ load resistor betw	een VDD and VL1	-1.15	-1.05	-0.95	V
		(without panel load)		-1.15	-1.05	-0.95	v
	VL2	Connect $1M\Omega$ load resistor betw	een VDD and VL2	2•VL1-0.1		2•VL1×0.85	V
		(without panel load)		2.01-0.1		2.0110.05	v
	VL3	Connect $1M\Omega$ load resistor betw	een VDD and VL3	3•V∟1-0.1		3•VL1×0.85	V
		(without panel load)		3°VL1-0.1		3°VL1×0.03	v
SVD voltage	Vsvd			-1.30	-1.20	-1.10	V
SVD circuit response time	tsvd					100	μS
Current consumption	IOP	During HALT			15.0	35.0	μA
		During execution *1	Without panel load		18.0	40.0	μΑ

\*1: The SVD circuit is turned off.



## Oscillation Characteristics

The oscillation characteristics change depending on the conditions (components used, board pattern, etc.). Use the following characteristics as reference values.

## E0C6S27 (Crystal)

(Unless	otherwis	e specified: VDD=0V, Vss=-3.0V, Crystal: C-002R (	CI=35kΩ), (	CG=25pF, C	D=built-in,	Га=25°С)
Characteristic	Symbol	Condition	Min.	Тур.	Max.	Unit
Oscillation start voltage	Vsta	tsta≤5sec (Vss)	-2.2			V
Oscillation stop voltage	Vstp	tstp≤10sec (Vss)	-2.2			V
Built-in capacitance (drain)	CD	Including the parasitic capacity inside the IC		20		pF
Frequency/voltage deviation	∂f/∂V	Vss=-1.8 to -3.6V			5	ppm
Frequency/IC deviation	∂f/∂IC		-10		10	ppm
Frequency adjustment range	∂f/∂Cg	CG=5 to 25pF	40			ppm
Harmonic oscillation start voltage	Vhho	CG=5pF (Vss)			-3.6	V
Permitted leak resistance	Rleak	Between OSC1 and VDD, Vss	200			MΩ

### E0C6SL27 (Crystal)

(Unless otherwise specified	ed: VDD=0V, Vss=-1.5V	, Crystal: C-002R (CI=35kΩ)	, CG=25pF, CD=built-in, Ta=25°	°C)

Symbol	Condition	Min.	Тур.	Max.	Unit
Vsta	tsta≤5sec (Vss)	-1.1			V
Vstp	tstp≤10sec (Vss)	-1.1(-0.9)*1			V
CD	Including the parasitic capacity inside the IC		20		pF
∂f/∂V	Vss=-1.1 to -1.8V (-0.9) *1			5	ppm
∂f/∂IC		-10		10	ppm
∂f/∂Cg	CG=5 to 25pF	40			ppm
Vhho	Cg=5pF (Vss)			-1.8	V
Rleak	Between OSC1 and VDD, Vss	200			MΩ
	Vsta Vstp CD ∂f/∂V ∂f/∂IC ∂f/∂CG Vhho	Vsta         tsta≤5sec         (Vss)           Vstp         tstp≤10sec         (Vss)           CD         Including the parasitic capacity inside the IC           ∂f/∂V         Vss=-1.1 to -1.8V (-0.9) *1           ∂f/∂IC            ∂f/∂CG         CG=5 to 25pF           Vhho         CG=5pF	Vsta         tsta≤5sec         (Vss)         -1.1           Vstp         tstp≤10sec         (Vss)         -1.1(-0.9)*1           CD         Including the parasitic capacity inside the IC	Vsta         tsta≤5sec         (Vss)         -1.1           Vstp         tstp≤10sec         (Vss)         -1.1(-0.9)*1           Cp         Including the parasitic capacity inside the IC         20           ∂f/∂V         Vss=-1.1 to -1.8V (-0.9) *1         -10           ∂f/∂IC         -10         -10           ∂f/∂CG         CG=5 to 25pF         40           Vhno         CG=5pF         (Vss)	Vsta         tsta≤5sec         (Vss)         -1.1           Vstp         tstp≤10sec         (Vss)         -1.1(-0.9)*1           CD         Including the parasitic capacity inside the IC         20           ∂f/∂V         Vss=-1.1 to -1.8V (-0.9) *1         5           ∂f/∂IC         -10         10           ∂f/∂CG         CG=5 to 25pF         40           Vhno         CG=5pF         (Vss)         -1.8

\*1: Items enclosed in parentheses () are those used when operating at heavy load protection mode.

## E0C6SB27 (Crystal)

Frequency adjustment range

Harmonic oscillation start voltage

(Unless otherwise specified: VDD=0V, Vss=-1.5V, Crystal: C-002R (Ci=35kΩ), CG=25pF, CD=built-in, Ta=25°C								
Characteristic	Symbol	Condition		Min.	Тур.	Max.	Unit	
Oscillation start voltage	Vsta	tsta≤5sec (Vs	ss)	-1.1			V	
Oscillation stop voltage	Vstp	tstp≤10sec (Vs	ss)	-1.1(-0.9)*1			V	
Built-in capacitance (drain)	CD	Including the parasitic capacity inside the IC			20		pF	
Frequency/voltage deviation	∂f/∂V	Vss=-1.1 to -3.6V (-0.9) *1				5	ppm	
Frequency/IC deviation	∂f/∂IC			-10		10	ppm	
Frequency/IC deviation	di/diC			-10		10	ppm	

Between OSC1 and VDD, VSS Permitted leak resistance Rleak 200 \*1: Items enclosed in parentheses ( ) are those used when operating at heavy load protection mode.

CG=5 to 25pF

CG=5pF

∂f/∂Cg

Vhho

### E0C6S27 (CR)

		(Unless otherwise spe	ecified: V	/dd=0V, Vss	s=-3.0V, Rc	R=470kΩ, 1	⁻a=25°C)
Characteristic	Symbol	Condition		Min.	Тур.	Max.	Unit
Oscillation frequency dispersion	fosc			-20	65kHz	20	%
Oscillation start voltage	Vsta		(Vss)	-2.2			V
Oscillation start time	tsta	Vss=-2.2 to -3.6V			3		mS
Oscillation stop voltage	Vstp		(Vss)	-2.2			V

## E0C6SA27 (CR)

			(Unless otherwise specified: \		= 3.0 V Rc		[a_25°€)
Characteristic	Symbol		Condition	Min.	 Typ.	Max.	Unit
Oscillation frequency dispersion	fosc			-30	200kHz	30	%
Oscillation start voltage	Vsta		(Vss)	-2.2			V
Oscillation start time	tsta	Vss=-2.2 to -3.6V			3		mS
Oscillation stop voltage	Vstp		(Vss)	-2.2			V

## E0C6SB27 (CR)

## (Unless otherwise specified: VDD=0V, Vss=-1.5V, Rcr=470kΩ, Ta=25°C)

40

(Vss)

Characteristic	Symbol	Condition	Min.	Тур.	Max.	Unit
Oscillation frequency dispersion	fosc		-20	65kHz	20	%
Oscillation start voltage	Vsta	(Vss)	-1.1			V
Oscillation start time	tsta	Vss=-1.1 to -3.6V		3		mS
Oscillation stop voltage	Vstp	(Vss)	-1.1			V



ppm

V

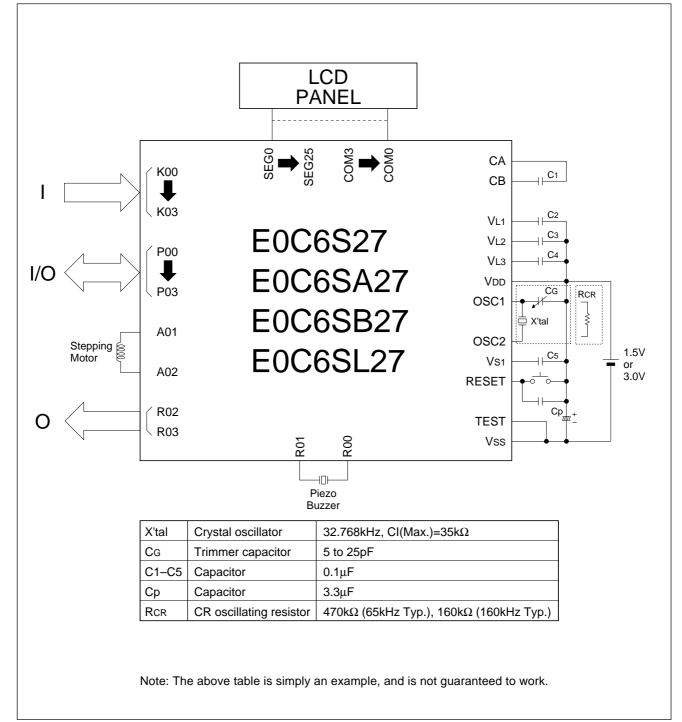
MΩ

-3.6

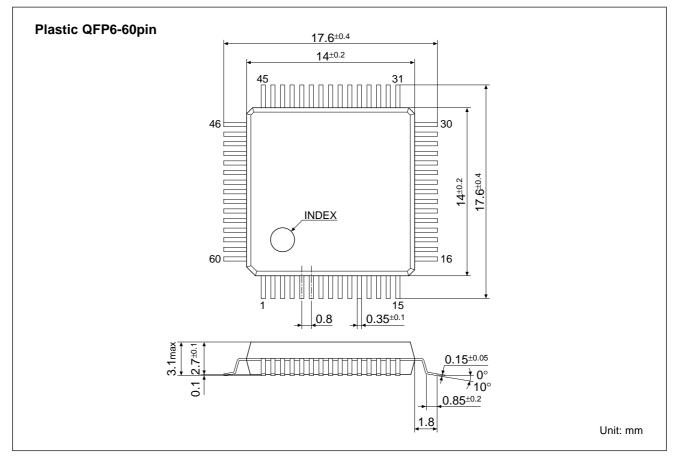
## Motor Driver Characteristics

(Unless otherwise specified: VDD=0V, Vss=-1.58V, Crystal: C-002R (CI=35kΩ), CG=25pF, CD=built-in, Ta=25°C)							
Characteristic	Symbol	Condition	Min.	Тур.	Max.	Unit	
Output voltage	Vout	Vss=-1.35V RL=2kΩ	1.15			V	
Diode characteristic	ID	Vn=0.6V	10			μA	
Output driver leak (Pch)	lleak				1	MΩ	

## ■ BASIC EXTERNAL CONNECTION DIAGRAM



## PACKAGE DIMENSIONS



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